CONTENTS

Preface ix

SECTION I. PLENARY SESSIONS

Current state and future challenge in molecular beam epitaxy (MBE) research
A.Y. Cho 1
Current understanding of growth mechanisms in III–V MBE
C.T. Foxon 11
Migration-enhanced epitaxy of GaAs and AlGaAs
Y. Horikoshi and M. Kawashima 17

SECTION II. GROWTH KINETICS AND RELATED PHENOMENA

On the origin of RHEED intensity oscillations
G.S. Petrich, P.R. Pukite, A.M. Wowchak, G.J. Whaley, P.I. Cohen and A.S. Arrott 23
Influence of surface morphology upon recovery kinetics during interrupted expitaxial growth
S. Clarke, D.D. Vvedensky and M.W. Ricketts 28
Low-temperature selective growth of GaAs by alternately supplying molecular beam epitaxy
S. Yokoyama, J. Oogi, D. Yui and M. Kawabe 32
Surface segregation of third-column atoms in III–V ternary arsenides
F. Houzay, J.M. Moison, C. Guille, F. Barthe and M. Van Rompay 35
TEM investigation of modulated structures and ordered structures in InAlAs crystals grown on (001) InP substrates by molecular beam epitaxy
O. Ueda, T. Fujii, Y. Nakada, H. Yamada and I. Umebu 38
Atomic ordering in $GaAs_{0.5}Sb_{0.5}$ grown by molecular beam epitaxy
N. Otsuka, Y.E. Ihm, Y. Hirotsu, J. Klem and H. Morkoç 43
Simulation of MBE growth
J.L. Beeby 48
Effects of growth interruption on structure of MBE grown GaAs/AlAs hetero-interfaces studied by X-ray diffraction
S. Koshiba, S. Nanao, O. Tsuda, Y. Watanabe, Y. Sakurai, H. Sakaki, H. Kawata and M. Ando 51
Simulation of epitaxial growth over patterned substrates
M. Ohtsuka and A. Suzuki 55
Electron mobility and roughness scattering in potential inserted quantum wells (PI-QWs)
T. Noda, M. Tanaka and H. Sakaki 60
Near surface transition layer model of MBE growth
M.A. Herman 64
Surface diffusion effects in MBE growth of QWs on channeled substrate (100) GaAs for lasers
H.P. Meier, E. Van Gieson, P.W. Epperlein, C. Harder, W. Walter, M. Krahl and D. Bimberg 66
Anisotropic surface migration of Ga atoms on GaAs (001)
K. Ohta, T. Kojima and T. Nakagawa 71
Interface roughness and confined LO phonons in quantum wells
G. Fasol, M. Tanaka, H. Sakaki and Y. Horikoshi 75

SECTION III. GaAs ON Si AND RELATED SYSTEMS

Electronic and optical devices with gallium arsenide on silicon prepared by MBE
H. Morkoç 79

Optimized growth start and controlled formation of misfit dislocations for heteroepitaxial GaAs on (100) Si grown by migration-enhanced epitaxy
W. Stolz, Y. Horikoshi, M. Naganuma and K. Nozawa 87
Low-temperature cleaning of Si and growth of GaAs on Si by hydrogen plasma-assisted metalorganic molecular-beam epitaxy
Y. Kunitsugu, I. Suemune, Y. Tanaka, Y. Kan and M. Yamanishi 91
GaAs on Si and related systems: problems and prospects
H. Kroemer, T.Y.Liu and P.M. Petroff 96
Initial stage of epitaxy of GaAs on Si
M. Kawabe and T. Shiraishi 103
Lattice strain relaxation at the initial stages of heteroepitaxy of GaAs on(100)Si by molecular beam epitaxy
T. Yao, H. Nakao, H. Kawanami and R. Toba 107
Growth and characterization of GaAs films on porous Si
S. Hasegawa, K. Maehashi, H. Nakashima, T. Ito and A. Hiraki 113
Molecular beam epitaxy of single domain InP films directly grown on Si(001) substrates
H. Kawanami and Y. Hayashi 117

SECTION IV. GAS SOURCE MOMBE AND CBE

From chemical vapor epitaxy to chemical beam epitaxy
W.T. Tsang 121
Effect of exposure to group III alkyls on compound semiconductor surfaces observed by X-ray photoelectron spectroscopy
H. Ishii, H. Ohno, K. Matsuzaki and H. Hasegawa 132
Surface chemical kinetics during the growth of GaAs by chemical beam epitaxy
T.H. Chiu, J.E. Cunningham and A. Robertson, Jr. 136
Selective-area epitaxy of GaAs by molecular-beam epitaxy (MBE) and metalorganic MBE with excimer laser irradiation
C.W. Tu, V.M. Donnelly, J.C. Beggy, V.R. McCrary and J.A. McCaulley 140
Photo-assisted chemical beam epitaxy of GaAs
K. Nagata, Y. Iimura, Y. Aoyagi, S. Namba and S. Den 142
Heavily carbon doped p-type GaAs and GaAlAs grown by metalorganic molecular beam epitaxy
T. Yamada, E. Tokumitsu, K. Saito, T. Akatsuka, M. Miyauchi, M. Konagai and K. Takahashi 145
Growth parameter dependence of background doping level in GaAs, $In_{0.53}Ga_{0.47}As$ and $Al_xGa_{1-x}As$ grown by metalorganic molecular beam epitaxy
J.L. Benchimol, F. Alexandre, Y. Gao and F. Alaoui 150
Carbon incorporation in MOMBE-grown $Ga_{0.47}In_{0.53}As$
M. Kamp, R. Contini, K. Werner, H. Heinecke, M. Weyers, H. Lüth and P. Balk 154
MOMBE (metalorganic molecular beam epitaxy) growth of InGaSb on GaSb
T. Kaneko, H. Asahi, Y. Okuno and S. Gonda 158
Growth of (AlIn)P/GaAs single quantum well structure on (001) GaAs by gas source MBE using AsH_3 and PH_3 gas
S. Nagao, Y. Inoue, M. Katoh, K. Shimoyama and H. Gotoh 163
Selective area growth of indium phosphide based heterostructures by metalorganic molecular beam epitaxy
D.A. Andrews, M.A.Z. Rejman-Greene, B. Wakefield and G.J. Davies 167
Growth mechanism of $In_{1-x}Ga_xP$ and $In_{1-x}Al_xP$ in metalorganic molecular beam epitaxy
K. Ozasa, M. Yuri, S. Tanaka and H. Matsunami 171
Gas source MBE growth of InP
Y. Morishita, S. Maruno, M. Gotoda, Y. Nomura and H. Ogata 176
Sn doping for InP and InGaAs grown by metalorganic molecular beam epitaxy using tetraethyltin
Y. Kawaguchi and K. Nakashima 181
Very high purity GaAs grown by gas source molecular beam epitaxy
J.E. Cunningham, G. Timp, T.H. Chiu, J.A. Ditzenberger, W.T. Tsang, A.M. Sergent and D.V. Lang 185

SECTION V. STRAINED LAYER STRUCTURES

Electronic properties of two-dimensional electron gas in pseudomorphic $In_xGa_{1-x}As/N\text{-}In_{0.52}Al_{0.48}As$ heterostructures
S. Sasa, Y. Nakata, Y. Sugiyama, T. Fujii and E. Miyauchi 189
Growth phenomena and characteristics of strained in $In_xGa_{1-x}As$ on GaAs
J. Pamulapati, P. Berger, K. Chang, J. Oh, Y. Chen, J. Singh, P. Bhattacharya and R. Gibala 193

Effects of strain and surface reconstruction on the kinetics of indium incorporation in MBE growth of InAs
K.R. Evans, C.E. Stutz, D.K. Lorance and R.L. Jones 197
Effects of the elastic strains and relaxations on In-incorporation in (Al, In)As pseudomorphic layers grown by molecular beam epitaxy
F. Turco, A.A. Mbaye and J. Massies 201
Structural and optical studies on molecular beam epitaxially grown $(InAs)_m(AlAs)_m$ and $(InAs)_m(GaAs)_m$ short-period strained layer superlattices
K. Nishi, T. Anan, Y. Ide and K. Onabe 202
High-quality AlGaAs/GaAs quantum well with a short period (InGaAs)(GaAs) strained superlattice buffer layer
F. Sato, H. Imamoto, K. Imanaka and M. Shimura 206
MBE growth of InAs/AlInAs strained-layer multi quantum wells for optical device applications
Y. Matsushima, H. Kato, K. Utaka and K. Sakai 210
Hot carrier photoluminescence from strained $In_xGa_{1-x}As/GaAs$ single quantum wells
T.G. Andersson, Z.-G. Chen, Z.-Y. Xu, J.-Z. Wu and W.-K. Ge 215
MBE growth of pseudomorphic $GaAs_ySb_{1-y}$ in a GaAs host lattice
G.I. Hobson, B. Khamsehpour, K.E. Singer and W.S. Truscott 220
RHEED and X-ray characterization of InGaAs/GaAs grown by MBE
Sz. Fujita, Y. Nakaoka, T. Uemura, M. Tabuchi, S. Noda, Y. Takeda and A. Sasaki 224
Interfacial studies and electrical characterisation of heteroepitaxial InSb on GaAs (100) grown by MBE
C.F. McConville, C.R. Whitehouse, G.M. Williams, A.G. Cullis, T. Ashley, M.S. Skolnick, G.T. Brown and S.J. Courtney 228
Heteroepitaxy of InAs quantum wells
H. Munekata, T.P. Smith III and L.L. Chang 235
Stress relief in patterned GaAs grown on mismatched substrates
B.G. Yacobi, S. Zemon, C. Jagannath and P. Sheldon 240
Growth and characterization of in-situ (In, Ga)As ohmic contacts to n-GaAs
S.L. Wright, R.F. Marks, E.D. Marshall, Y.C. Shih and A.B. Young 245

SECTION VI. MODULATION DOPED STRUCTURES

Growth and doping of heterostructures for high electron mobilities
A.C. Gossard, J.H. English, M. Miller and R.J. Simes 247
MBE growth of two-dimensional electron system with extremely low disorder
M. Shayegan, V.J. Goldman, T. Sajoto, M. Santos, C. Jiang and H. Ito 250
Spatial localization of Si in selectively δ-doped $Al_xGa_{1-x}As/GaAs$ heterostructures for high mobility and density realization
J.E. Cunningham, G. Timp, A.M. Chang, T.H. Chiu, W. Jan, E.F. Schubert and W.T. Tsang 253
Si migration effects in GaAs/(Al, Ga)As heterojunction and δ-doped structures
J.J. Harris, R.B. Beall, J.B. Clegg, C.T. Foxon, S.J. Battersby, D.E. Lacklison, G. Duggan and C.M. Hellon 257

SECTION VII. NOVEL LOW-DIMENSIONAL STRUCTURE, GROWTH OF VICINAL SURFACES AND DOPING

Band gap modulation in two dimensions by MBE growth of tilted superlattices and applications to quantum confinement structures
P.M. Petroff, J. Gaines, M. Tsuchiya, R. Simens, L. Coldren, H. Kroemer, J. English and A.C. Gossard 260
One- and zero-dimensional systems: fabrication and characterization
J.M. Hong, T.P. Smith III, K.Y. Lee, C.M. Knoedler, S.E. Laux, D.P. Kern and L. Esaki 266
The meandering of steps on GaAs(100)
P.R. Pukite, G.S. Petrich, S. Batra and P.I. Cohen 269
Surface diffusion during MBE growth of GaAs–AlGaAs single quantum wells on vicinal surfaces
K. Kanamoto, K. Fujiwara, Y. Tokuda, N. Tsukada, M. Ishii and T. Nakayama 273
Optical properties of thermally interdiffused MBE-grown GaAs/GaAlAs quantum wells
H. Leier, H. Rothfritz, A. Forchel and G. Weimann 277
Lattice-matched and lattice-mismatched growth on novel GaAs substrate orientations
P.N. Uppal, J.S. Ahearn, S.P. Svensson and R. Herring 281
X-ray diffraction effects in Ga and Al arsenide structures MBE-grown on slightly misoriented GaAs (001) substrates
P. Auvray, M. Baudet and A. Regreny 288

Comparison of RHEED during MBE growth and the quality of AlGaAs : Si grown on (100) and misoriented GaAs substrates
H. Lee, N. Nouri, C. Colvard and D. Ackley 292
Trap gettering by isoelectronic doping of p-GaAs and n-GaAs grown by molecular beam epitaxy
Aizhen Li, H.K. Kim, J.C. Jeong, D. Wong, J.H. Zhao, Z.-Q. Fang, T.E. Schlesinger and A.G. Milnes 296
Influence of As_4/Ga flux ratio on Be incorporation in heavily doped GaAs grown by molecular beam epitaxy
Y.C. Pao, J. Franklin and J.S. Harris, Jr. 301
Molecular beam epitaxy AlGaAs/GaAs grown in the presence of hydrogen
Y.C. Pao, D. Liu and J.S. Harris, Jr. 305

SECTION VIII. MBE FOR PRODUCTION AND RELATED TECHNOLOGY

MBE as a production technology for HEMT LSIs
K. Kondo, J. Saito, T. Igarashi, K. Nanbu and T. Ishikawa 309
Ultra-high throughput of GaAs and (AlGa)As layers grown by MBE with a specially designed MBE system
T. Sonoda, M. Ito, M. Kobiki, K. Hayashi, S. Takamiya and M. Mitsui 317
In situ cleaning of GaAs substrates with HCl gas and hydrogen mixture prior to MBE growth
J. Saito, K. Nanbu, T. Ishikawa and K. Kondo 322

SECTION IX. OPTICAL PROPERTIES OF QUANTUM WELLS AND TUNNELING

Recent developments in optical processes in quantum wells and superlattices: many body effects and field-induced localization
M. Voos 328
MBE growth and properties of (100)- and (111)-oriented GaInP/AlInP quantum wells on GaAs substrates
K. Takahashi, T. Hayakawa, M. Hosoda, S. Yamamoto and T. Hijikata 333
Optical properties of high-quality InAlAs/InGaAs SQWs grown by MBE using specially refined In and Al sources
T. Mishima, J. Kasai, Y. Uchida and S. Takahashi 338
Molecular beam epitaxial growth of $(Al_yGa_{1-y})_xIn_{1-x}P$ ($x \sim 0.5$) on (100) GaAs
T. Hayakawa, K. Takahashi, K. Sasaki, S. Yamamoto and T. Hijikata 343
High on/off ratio bistable operation of InGaAs/InAlAs MQW lasers using resonant tunneling effect
Y. Kawamura, K. Wakita and O. Mikami 348
Investigation of asymmetric double barrier resonant tunneling structures based on (AlGa)As/GaAs
O.H. Hughes, M. Henini, E.S. Alves, L. Eaves, M.L. Leadbeater, F.W. Sheard, G. Hill, M.A. Pate, J.C. Portal and A. Celeste 352
Tunneling of X-point electrons in triple barrier diodes
T. Nakagawa, T. Kojima and K. Ohta 357

SECTION X. CURRENT STATE OF MOCVD AND BAND DISCONTINUITY STUDY

MOCVD – current state and future
H. Kukimoto 360
Conduction-band edge discontinuity of InGaAs/GaAsSb heterostructures lattice-matched to InP grown by molecular beam epitaxy
Y. Sugiyama, T. Fujii, Y. Nakata, S. Muto and E. Miyauchi 363
Absence of growth sequence dependence of AlAs/GaAs heterojunction band discontinuity determined by X-ray photoelectron spectroscopy
H. Ohno, H. Ishii, K. Matsuzaki and H. Hasegawa 367
Determination of the resonant-state energy of an $In_{0.53}Ga_{0.47}As$/AlAs pseudomorphic resonant tunneling barrier grown by MBE
T. Inata, S. Muto, S. Sasa and E. Miyauchi 371

SECTION XI. MBE-GROWN DEVICES

Distributed feedback (DFB) lasers at 1.5 μm grown by gas source molecular beam epitaxy (GSMBE)
L. Goldstein, C. Artique, D. Bonnevie, B. Fernier, A. Perales and J. Benoit 375

AlInAs/GaInAs HEMT application for high performance OEIC receivers
O. Wada, H. Nobuhara, M. Makiuchi, H. Hamaguchi, S. Sasa and T. Fujii 378
Low temperature MBE growth of high quality modulation doped AlGaAs/GaAs MQWs for ultra-high-speed laser diodes
T. Mishima, T. Tanoue and K. Uomi 382
Observation of microwave oscillations (up to 32.6 GHz) from biwell superlattice devices
Y. Tanaka, H. Kano, M. Hashimoto and I. Igarashi 386
Growth and properties of N-AlGaAs/InGaAs selectively-doped single- and double-heterojunction FET structures
T. Matsuno, K. Nishii and K. Inoue 390
Highly-sensitive Hall element with quantum-well superlattice structures
Y. Sugiyama, H. Soga and M. Tacano 394

SECTION XII. GaAs-RELATED NOVEL HETEROSTRUCTURES

Growth of single domain GaAs/fluoride/Si structures
K. Tsutsui, T. Asano, H. Ishiwara and S. Furukawa 398
Reduction of strain in GaAs grown on CaF_2/Si heteroepitaxial substrates
S. Hashimoto, W.M. Gibson, L.J. Schowalter, E.Y. Lee and P.A. Claxton 403
Molecular beam epitaxial growth of high quality GaAs layer directly on GaP substrate
M. Tsuji, Y. Takano, T. Torihata, Y. Kanaya, K. Pak and H. Yonezu 405
Growth of single-crystal Fe/Cr magnetic multilayer structures on (001) GaAs by molecular beam epitaxy
P. Etienne, J. Chazelas, G. Creuzet, A. Friederich, J. Massies, F. Nguyen-Van-Dau and A. Fert 410
Initial stage of CaF_2 heteroepitaxy on GaAs(001) substrates
T. Waho, F. Yanagawa and Y. Yamada 415
Doping properties of Ge and GaAs (100) grown by MBE
M. Kawanaka and J. Sone 421
MBE growth of AlGaAs/NiAl/AlGaAs heterostructures: a novel epitaxial III–V semiconductor/metal system
J.P. Harbison, T. Sands, N. Tabatabaie, W.K. Chan, L.T. Florez and V.G. Keramidas 425
Growth of Ni_3Ga_2, NiGa and Ni_2Ga_3 on GaAs (001) and (111) in molecular beam epitaxy system
A. Guivarc'h, J. Caulet, B. Guenais, Y. Ballini, R. Guérin, A. Poudoulec and A. Regreny 427

SECTION XIII. Si–Ge HETEROSTRUCTURES

Silicon/germanium strained layer superlattices
G. Abstreiter, K. Eberl, E. Friess, W. Wegschneider and R. Zachai 431
Growth of abrupt Ge layers in Si(100)
S.S. Iyer, P.R. Pukite, J.C. Tsang and M.W. Copel 439
Ge_m/Si_m strained-layer superlattices fabricated by phase-locked epitaxy
K. Miki, K. Sakamoto, T. Sakamoto, H. Okumura, N. Takahashi and S. Yoshida 444
Epitaxy of Si–Ge heterostructures by Si MBE
J.-M. Baribeau, D.C. Houghton, D.J. Lockwood, M.W.C. Dharma-Wardana and G.C. Aers 447
Study of ultra-thin Ge/Si strained layer superlattice
S.J. Chang, C.F. Huang, M.A. Kallel, K.L. Wang, R.C. Bowman, Jr. and P.M. Adams 451

SECTION XIV. Si, SILICIDES AND RELATED COMPOUNDS

Growth of single crystal $CoSi_2$ layers at room temperature
R.T. Tung and F. Schrey 455
Atomic layer epitaxy of cubic SiC by gas source MBE using surface superstructure
T. Fuyuki, M. Nakayama, T. Yoshinobu, H. Shiomi and H. Matsunami 461
Preparation and characterization of SiN_x films epitaxially grown on Si(111) substrates
T. Ichimori, M. Tabe and Y. Sakakibara 464
Microscopic observation of Si MBE on Si(001) surface using microprobe RHEED
T. Doi and M. Ichikawa 468
RHEED intensity rocking curves from Si(111) surface during MBE growth
H. Nakahara and A. Ichimiya 472

Disilane gas source Si-MBE
H. Hirayama, T. Tatsumi and N. Aizaka 476
Atomic layer doping (ALD) technology in Si and its application to a new structure FET
A.A. van Gorkum, K. Nakagawa and Y. Shiraki 480
Verry low temperature growth and doping of silicon MBE layers
H. Jorke, H. Kibbel, F. Schäffler, A. Casel, H.-J. Herzog and E. Kasper 484
Measurement and mechanism of free carrier recombination in a silicon doping superlattice
K.H. Teo, J.N. McMullin, F.L. Weichman, H.G. Schmidt-Weinmar, D. Landheer and M.W. Denhoff 486
Self-aligned $NiSi_2$ electrode fabrication by MBE and its application to etched-groove permeable base transistor (PBT)
T. Ohshima, K. Nakagawa, N. Nakamura and Y. Shiraki 490
Metalorganic molecular beam epitaxy of γ-Al_2O_3 insulator films on Si with laser irradiation
K. Sawada, M. Ishida, T. Nakamura and T. Suzaki 494
Development of a new MBE growth method for fabrication of high quality, double epitaxial Si/γ-Al_2O_3/Si structures
H. Ogata, H. Hanafusa and K. Yoneda 500
Formation and structures of NiO–ZnO artificial superlattices
K. Iijima, T. Terashima, K. Yamamoto and Y. Bando 505

SECTION XV. II–VI COMPOUNDS

Homoepitaxial growth of low-resistivity-Al-doped ZnS single crystal films by molecular beam epitaxy
M. Kitagawa, Y. Tomomura, A. Suzuki and S. Nakajima 509
Growth of p- and n-type ZnSe by molecular beam epitaxy
H. Cheng, J.M. DePuydt, J.E. Potts and M.A. Haase 512
Growth and characterization of MBE-grown ZnTe : P
Y. Hishida, H. Ishii, T. Toda and T. Niina 517
Growth of ZnSe films on GaAs ⟨100⟩ substrates by conventional and pulsed molecular beam epitaxy
J. Lilja, J. Keskinen, H. Asonen and M. Pessa 522
Lattice strain and its effect of energy band structure in MBE-$ZnSe_xSe_{1-x}$/GaAs
N. Matsumura, M. Tsubokura and J. Saraie 525
MBE growth mechanisms of ZnSe: flux ratio and substrate temperature
Z. Zhu, T. Nomura, M. Miyao and M. Hagino 529
Incorporation processes in MBE growth of ZnSe
R. Venkatasubramanian, N. Otsuka, J. Qiu, L.A. Kolodziejski and R.L. Gunshor 533
Photo-assisted MBE growth on ZnSe crystals
M. Ohishi, H. Saito, H. Okano and K. Ohmori 538
Properties of undoped and Sb-doped CdTe surfaces prepared by conventional and photo-assisted molecular beam epitaxy
J.D. Benson, D. Rajavel, B.K. Wagner, R. Benz II and C.J. Summers 543
MBE-grown ZnTe–ZnS strained-layer superlattices
T. Karasawa, K. Ohkawa and T. Mitsuyu 547
Twin free growth of II–VI compounds on (111) CdZnTe substrates by molecular beam epitaxy
L. Di Cioccio, A. Million, J. Piaguet, G. Rolland, G. Lentz, N. Magnea and H. Mariette 552
MBE growth of CdTe and $Cd_{1-x}Mn_xTe$ layers and multilayers on InSb substrates
D.E. Ashenford, B. Lunn, J.J. Davies, J.H.C. Hogg, J.E. Nicholls, C.G. Scott, D. Shaw, H.H. Sutherland, C.P. Hilton, T.J. Gregory and D. Johnston 557
Epitaxial lead chalcogenides on fluoride covered silicon substrates: properties and infrared device fabrication
H. Zogg, C. Maissen, J. Masek and S. Blunier 562
Growth of CdTe/α-Sn/CdTe/InSb multilayer structure by MBE
S. Satoh and M. Kimata 564
II–VI/III–V heterointerfaces: epilayer-on-epilayer structures
Q.-D. Qian, J. Qiu, J.L. Glenn, Sungki O, R.L. Gunshor, L.A. Kolodziejski, M. Kobayashi, N. Otsuka, M.R. Melloch, J.A. Cooper, Jr., M. Haggerott, T. Heyen and A.V. Nurmikko 567
A study of growth mechanism of ZnS and ZnSe in MOMBE using dimethylzinc and chalcogen hydrides as reactants
A. Yoshikawa, H. Oniyama, S. Yamaga and H. Kasai 572
Atomic layer epitaxy of ZnSe–ZnTe strained layer superlattices
S. Dosho, Y. Takemura, M. Konagai and K. Takahashi 580
Growth and characterization of CdTe single quantum wells confined by $Cd_{1-x}Zn_xTe$ alloy and short period CdTe/ZnTe superlattice
N. Magnea, G. Lentz, H. Mariette, G. Feuillet, F. Dal'bo and H. Tuffigo 584

SECTION XVI. II–VI AND OTHER NOVEL MATERIAL SYSTEMS

Physics and engineering of diluted magnetic semiconductor supperlattices
A.V. Nurmikko, L.A. Kolodziejski and R.L. Gunshor 589
MBE growth and characterization of Hg-based superlattices
O.K. Wu, F.A. Shirland, J.P. Baukus, J.N. Schulman, G.S. Kamath and E.A. Patten 594
Molecular beam epitaxial growth and photoluminescence of PbS–PbCdSSe single quantum wells
S. Hashimoto, N. Koguchi, S. Takahashi and S. Akiba 599
Application of Van der Waals epitaxy to highly heterogeneous systems
K. Saiki, K. Ueno, T. Shimada and A. Koma 603

SECTION XVII. HIGH T_c SUPERCONDUCTORS

MBE growth of high critical temperature superconductors
J.S. Harris, J.N. Eckstein, E.S. Hellmann and D.G. Schlomm 607
Formation and properties of $YBa_2Cu_3O_{7-x}$ single-crystal thin films by activated reactive evaporation
T. Terashima, K. Iijima, K. Yamamoto, J. Takada, K. Hirata, H. Mazaki and Y. Bando 617
In situ determinaton of Ba, Y, Cu and O_2 flux by cold cathode discharge induced emission spectroscopy
J. Sakai, K. Kato, K. Hirama, S. Murakami and T. Ishida 621

Author index 625
Subject index 635